2SK3748

N-Channel Power MOSFET 1500V, 4A, 7Ω, TO-3PF-3L



http://onsemi.com

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching
- High reliability (Adoption of HVP process)
- · Attachment workability is good by Mica-less package
- · Avalanche resistance guarantee

Specifications

Absolute Maximum Ratings at Ta=25°C

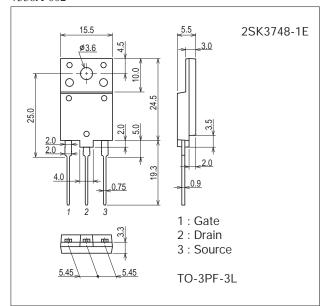
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1500	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID*		4	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8	А
Allowable Power Dissipation	D-		3.0	W
	PD	Tc=25°C	65	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		165	mJ
Avalanche Current *2	I _{AV}		4	А

^{*}Shows chip capability

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7538A-002



Product & Package Information

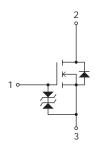
Package : TO-3PF-3LJEITA, JEDEC : SC-94

• Minimum Packing Quantity: 30 pcs./magazine

Marking

Electrical Connection





Semiconductor Components Industries, LLC, 2013

^{*1} V_{DD}=50V, L=20mH, I_{AV}=4A (Fig.1)

^{*2} L≤20mH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions	Ratings			Linit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.5		3.5	V
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =2A	1.7	2.8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =2A, V _G S=10V		5	7	Ω
Input Capacitance	Ciss			790		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		140		pF
Reverse Transfer Capacitance	Crss			70		pF
Turn-ON Delay Time	t _d (on)			17		ns
Rise Time	t _r	Con Fig 2		75		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		360		ns
Fall Time	t _f			116		ns
Total Gate Charge	Qg			80		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =4A		6.4		nC
Gate-to-Drain "Miller" Charge	Qgd			36		nC
Diode Forward Voltage	V _{SD}	IS=4A, VGS=0V		0.94	1.2	V
Reverse Recovery Time	t _{rr}	I _S =4A, V _G S=0V, dis/dt=100A/μs		340		ns

Fig.1 Avalanche Resistance Test Circuit

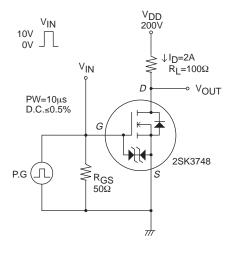
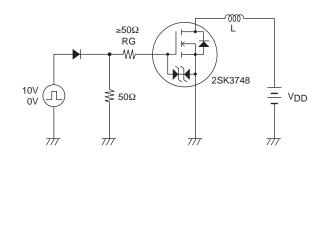
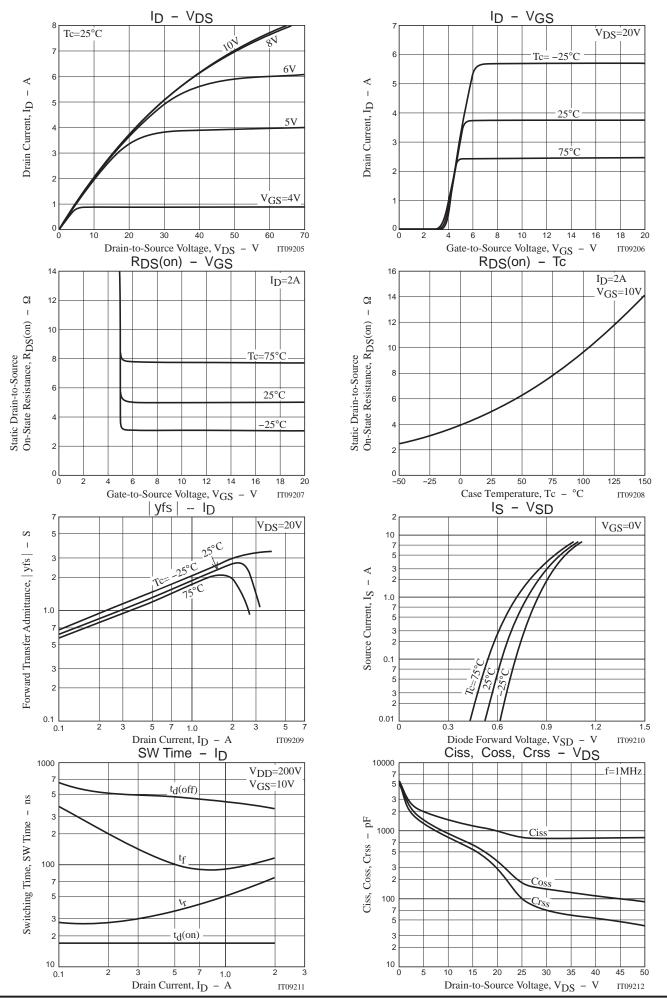


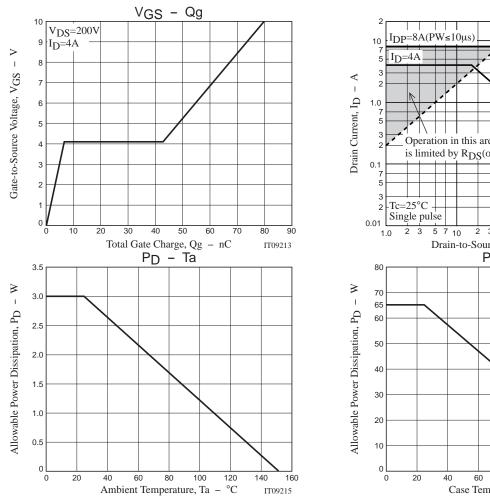
Fig.2 Switching Time Test Circuit

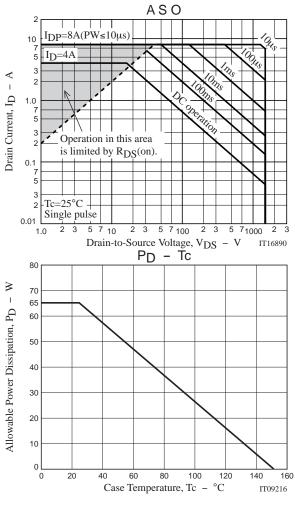


Ordering Information

Device	Package	Shipping	memo	
2SK3748-1E	TO-3PF-3L	30pcs./magazine	Pb Free	





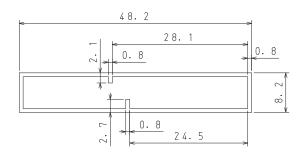


Magazine Specification

2SK3748-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format		
I acuaso Mamo	Magazine	Inner box	Outer box	Inner BOX	Outer BOX	
TO-3PF-3L	30	360	1440	SPD-0V0001 12 magazines contained Dimensions:mm(external) 568×150×55	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178	



Tolerance=±0.2mm
Thickness=0.8±0.2mm
Length =508.0±1mm
Material =PVC or PET
(Antistatic treatment)

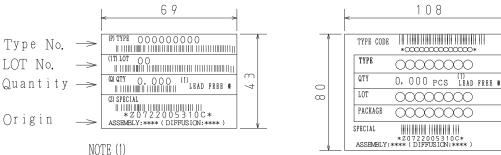
3. Storage method to magazine



4. Inner box label (unit:mm)



It is a label at the time of factory shipments. The form of a label may change in physical distribution process.

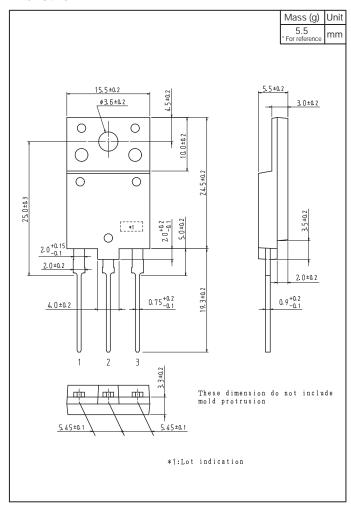


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK3748-1E



Note on usage: Since the 2SK3748 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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